

FDS6673BZ_F085 P-Channel PowerTrench[®] MOSFET -30V, -14.5A, 7.8mΩ

General Description

This P-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench process that has been especially tailored to minimize the on-state resistance.

This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

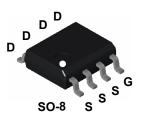
Features

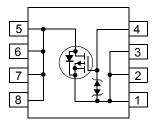
- Max $r_{DS(on)} = 7.8 m\Omega$, $V_{GS} = -10V$, $I_D = -14.5A$
- Max r_{DS(on)} = 12mΩ, V_{GS} = -4.5V, I_D = -12A
- Extended V_{GS} range (-25V) for battery applications
- HBM ESD protection level of 6.5kV typical (note 3)
- High performance trench technology for extremely low rDS(on)

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- High power and current handling capability
- RoHS compliant
- Qualified to AEC Q101





MOSFET Maximum Ratings $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DS}	Drain to Source Voltage		-30	V
V _{GS}	Gate to Source Voltage		±25	V
I _D	Drain Current -Continuous (No	ote1a)	-14.5	Α
	-Pulsed		-75	Α
P _D	Power Dissipation for Single Operation (N	ote1a)	2.5	
	(N	ote1b)	1.2	W
	(N	ote1c)	1.0	
T _J , T _{STG}	Operating and Storage Temperature		-55 to 150	°C

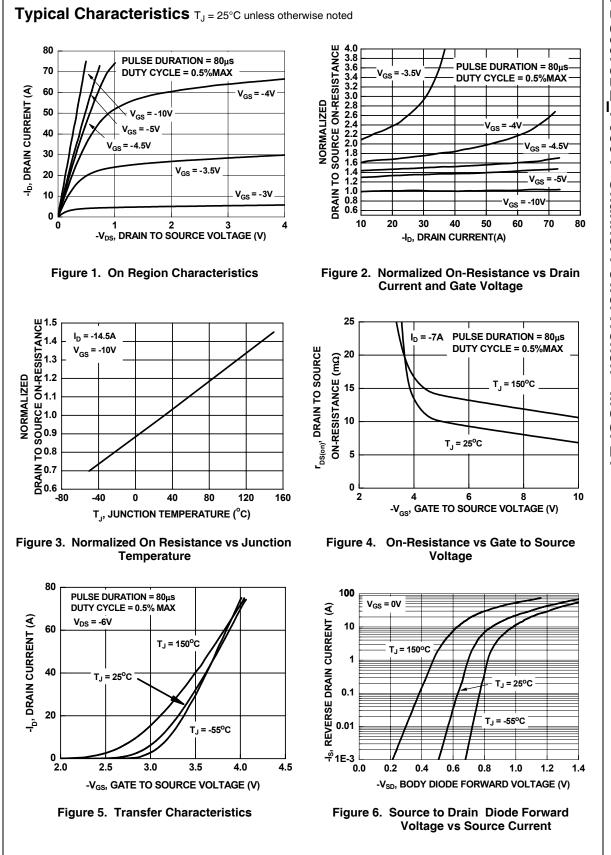
Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	°C/W
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case (Note 1)	25	°C/W

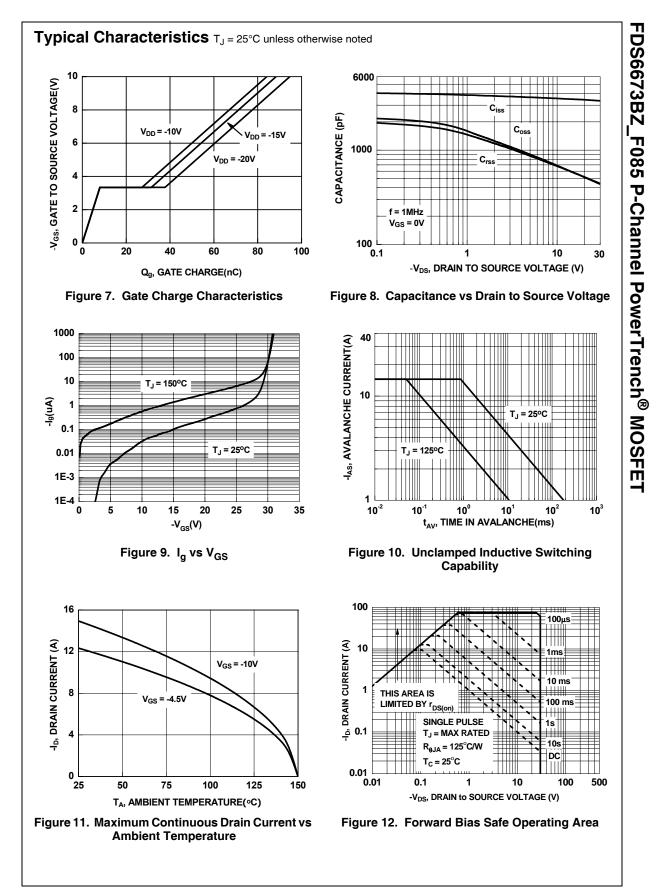
Package Marking and Ordering Information

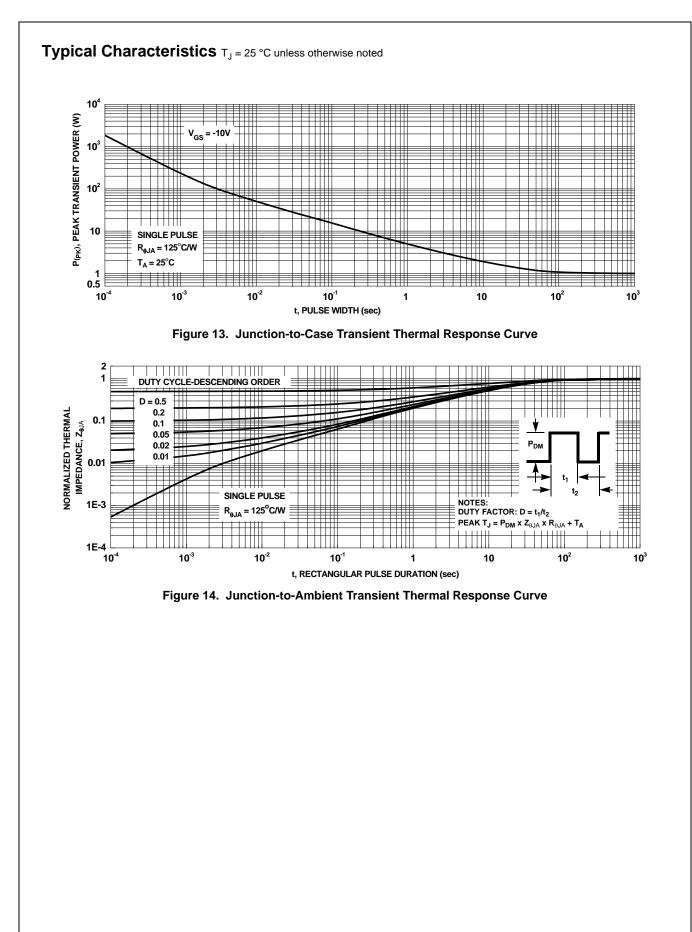
Device Marking	Device	Reel Size	Tape Width	Quantity
FDS6673BZ	FDS6673BZ_F085	13"	12mm	2500 units

	Parameter	Test Conditions	Min	Тур	Max	Units
	cteristics					
ΔB _{VDSS}	Drain to Source Breakdown Voltage	I _D = -250μA, V _{GS} = 0V	-30			V
ΔT_{I}	Breakdown Voltage Temperature	$I_D = -250\mu A$, referenced to $25^{\circ}C$		-20		mV/°C
	Zero Gate Voltage Drain Current	V _{DS} = -24V, V _{GS} = 0V			-1	μA
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 25V, V_{DS} = 0V$			±10	μΑ
		03 , D3 -				
On Charac	cteristics (Note 2)					
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = -250 \mu A$	-1	-1.9	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I _D = -250μA, referenced to 25°C		8.1		mV/°C
•		V _{GS} = -10V , I _D = -14.5A		6.5	7.8	
(DO()	Drain to Source On Resistance	V _{GS} = -4.5V, I _D = -12A		9.6	12	mΩ
DS(on)	Drain to Source On Resistance	V _{GS} = -10V, I _D = -14.5A T _J = 125°C		9.7	12	11122
9 _{FS}	Forward Transconductance	V _{DS} = -5V, I _D = -14.5A		60		S
-	Characteristics			I	1	
C _{iss}	Input Capacitance			3500	4700	pF
C _{oss}	Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$		600	800	pF
C _{rss}	Reverse Transfer Capacitance	f = 1.0MHz		600	900	pF
	Characteristics (Note 2)	<u> </u>				
t _{d(on)}	Turn-On Delay Time			14	26	ns
t _r	Rise Time	$V_{DD} = -15V, I_D = -1A$		16	29	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = -10V, R_{GS} = 6\Omega$		225	306	ns
t _f	Fall Time			105	167	ns
Q _g	Total Gate Charge	V _{DS} = -15V, V _{GS} = -10V, I _D = -14.5A		88	124	nC
Q _g	Total Gate Charge			46	65	nC
Q _{gs}	Gate to Source Gate Charge	$V_{DS} = -15V, V_{GS} = -5V,$		8		nC
Q _{gd}	Gate to Drain Charge	I _D = -14.5A		23.5		nC
J •	rce Diode Characteristics				1	1
Drain-Sou	Source to Drain Diode Forward Voltage	$V_{GS} = 0V, I_{S} = -2.1A$		-0.7	-1.2	V
Drain-Sou V _{SD}						
	Reverse Recovery Time	$I_F = 14.5A$, di/dt = 100A/µs			45	ns



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